

74AHC245; 74AHCT245

Octal bus transceiver; 3-state

Rev. 03 — 25 September 2007

Product data sheet

1. General description

The 74AHC/AHCT245 is a high-speed Si-gate CMOS device.

The 74AHC/AHCT245 is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions.

The 74AHC245/74AHCT245 features an Output Enable (\overline{OE}) input for easy cascading and a send/receive (DIR) input for direction control.

\overline{OE} controls the outputs so that the buses are effectively isolated.

2. Features

- Balanced propagation delays
- All inputs have a Schmitt-trigger action
- Inputs accepts voltages higher than V_{CC}
- For 74AHC245 only: operates with CMOS input levels
- For 74AHCT245 only: operates with TTL input levels
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1: Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AHC245D 74AHCT245D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHC245PW 74AHCT245PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHC245BQ 74AHCT245BQ	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85\text{ mm}$	SOT764-1

4. Functional diagram

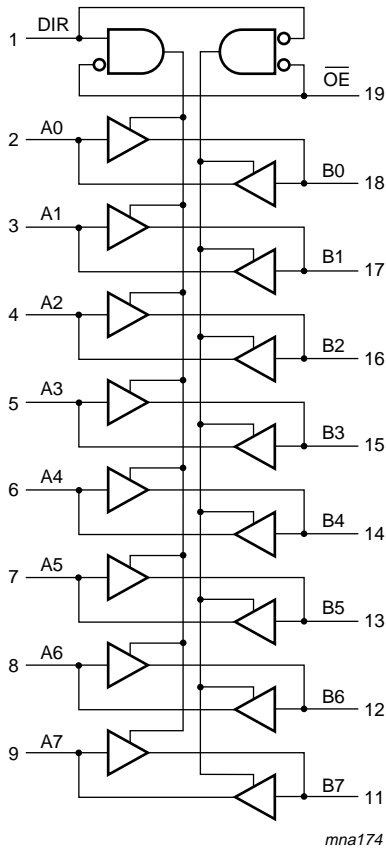


Fig 1. Logic symbol

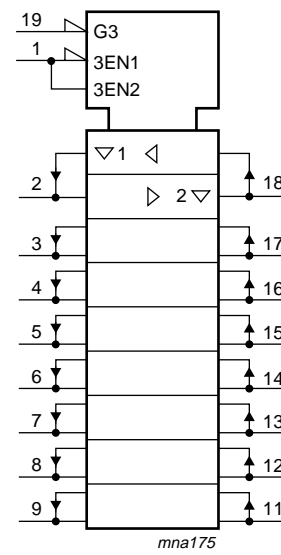
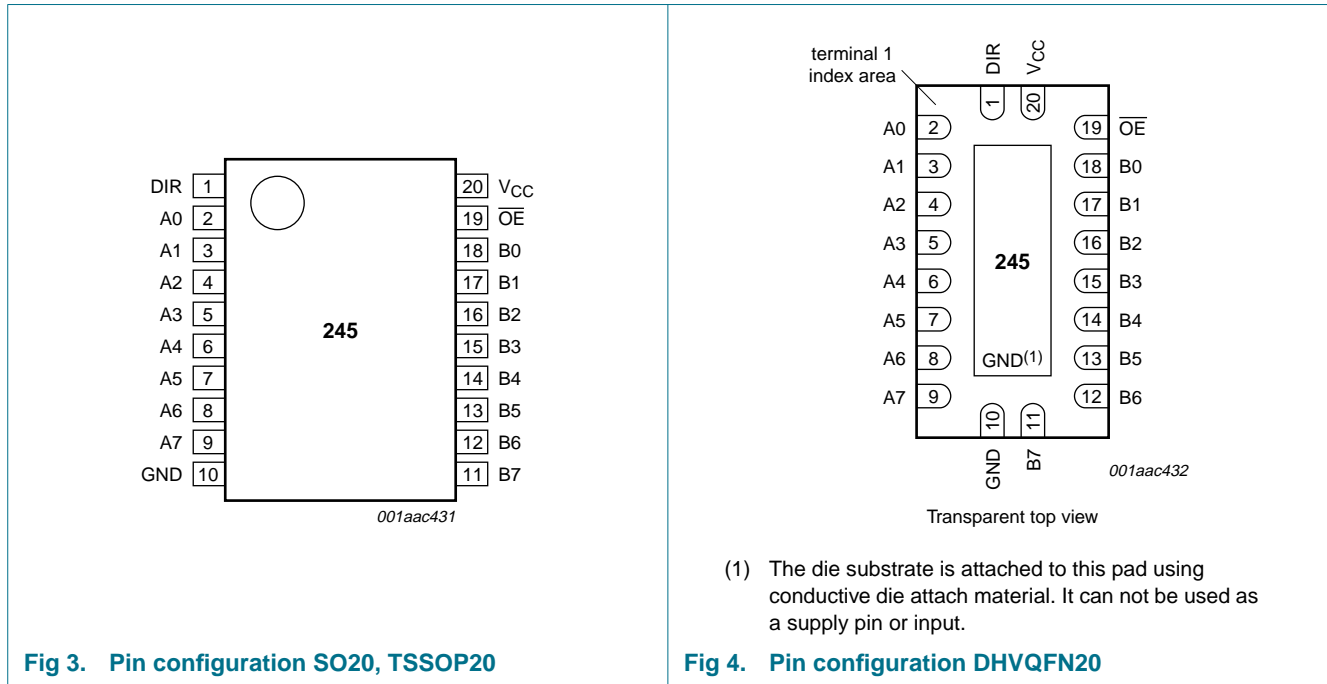


Fig 2. IEC logic symbol

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2: Pin description

Symbol	Pin	Description
DIR	1	direction control
A[0:7]	2, 3, 4, 5, 6, 7, 8, 9	data input/output
B[0:7]	18, 17, 16, 15, 14, 13, 12, 11	data input/output
GND	10	ground (0 V)
\overline{OE}	19	output enable input (active LOW)
V _{CC}	20	supply voltage

6. Functional description

Table 3: Function table^[1]

Input		Input/output		
$\overline{\text{OE}}$	DIR	An	Bn	
L	L	A = B	input	
L	H	input	B = A	
H	X	Z	Z	

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1] -20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1] -	±20	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)	-	±25	mA
I_{CC}	supply current		-	75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to $+125$ °C			
	SO20 package		[2] -	500	mW
	TSSOP20 package		[3] -	500	mW
	DHVQFN20 package		[4] -	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] P_{tot} derates linearly with 8 mW/K above 70 °C.
 [3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.
 [4] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC245			74AHCT245			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V _I	input voltage		0	-	5.5	0	-	5.5	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 3.3 V ± 0.3 V	-	-	100	-	-	-	ns/V
		V _{CC} = 5.0 V ± 0.5 V	-	-	20	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
For type 74AHC245										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -50 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -50 μA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = -50 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I _O = -8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.25	-	±2.5	-	±10.0	μA
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	4.0	-	40	-	80	μA

Table 6. Static characteristics ...continued
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C _I	input capacitance		-	3.0	10	-	10	-	10	pF
C _O	output capacitance		-	4.0	-	-	-	-	-	pF
For type 74AHCT245										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -50 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	per input pin; V _I = V _{IH} or V _{IL} ; V _{CC} = 5.5 V; I _O = 0 A V _O = V _{CC} or GND; other pins at V _{CC} or GND	-	-	±0.25	-	±2.5	-	±10.0	µA
I _I	input leakage current	V _I = V _{IH} or V _{IL} ; V _{CC} = 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	4.0	-	40	-	80	µA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} - 2.1 V; I _O = 0 A; other pins at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C _I	input capacitance		-	3	10	-	10	-	10	pF
C _O	output capacitance		-	4.0	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics
GND = 0 V. For test circuit see [Figure 7](#).

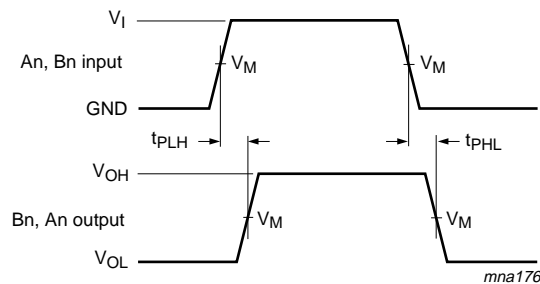
Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
For type 74AHC245										
t_{pd}	propagation delay	nAn to nYn; see Figure 5 ^[2]								
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$								
		$C_L = 15\text{ pF}$	-	5.0	8.4	1.0	10.0	1.0	10.5	ns
		$C_L = 50\text{ pF}$	-	6.5	11.9	1.0	13.5	1.0	15.0	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$								
		$C_L = 15\text{ pF}$	-	3.5	5.5	1.0	6.5	1.0	7.0	ns
t_{en}	enable time	nOE to nYn; see Figure 6 ^[2]								
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$								
		$C_L = 15\text{ pF}$	-	6.5	13.2	1.0	15.5	1.0	16.5	ns
		$C_L = 50\text{ pF}$	-	9.0	16.7	1.0	19.0	1.0	21.0	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$								
		$C_L = 15\text{ pF}$	-	4.0	8.5	1.0	10.0	1.0	11.0	ns
t_{dis}	disable time	nOE to nYn; see Figure 6 ^[2]								
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$								
		$C_L = 15\text{ pF}$	-	7.5	12.5	1.0	15.5	1.0	16.0	ns
		$C_L = 50\text{ pF}$	-	10.0	15.8	1.0	18.0	1.0	20.0	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$								
		$C_L = 15\text{ pF}$	-	4.5	7.8	1.0	9.2	1.0	10.0	ns
C_{PD}	power dissipation capacitance	$C_L = 50\text{ pF}; f_i = 1\text{ MHz}; V_i = \text{GND to }V_{CC}$ ^[3]	-	12	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued
GND = 0 V. For test circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
For type 74AHCT245										
t _{pd}	propagation delay	nAn to nYn; see Figure 5 ^[2]								
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.5	7.7	1.0	8.5	1.0	10.0	ns
		C _L = 50 pF	-	4.5	8.7	1.0	9.5	1.0	11.0	ns
t _{en}	enable time	nOE to nYn; see Figure 6								
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	5.0	13.8	1.0	15.0	1.0	17.5	ns
		C _L = 50 pF	-	6.0	14.8	1.0	16.0	1.0	18.5	ns
t _{dis}	disable time	nOE to nYn; see Figure 6 ^[2]								
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	5.0	14.4	1.0	15.5	1.0	18.0	ns
		C _L = 50 pF	-	6.0	15.4	1.0	16.5	1.0	19.5	ns
C _{PD}	power dissipation capacitance	per buffer; C _L = 50 pF; f = 1 MHz; V _I = GND to V _{CC}	^[3]	-	15	-	-	-	-	pF

- [1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
t_{en} is the same as t_{PZL} and t_{PZH}.
t_{dis} is the same as t_{PLZ} and t_{PHZ}.
- [3] C_{PD} is used to determine the dynamic power dissipation P_D (μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in Volts.

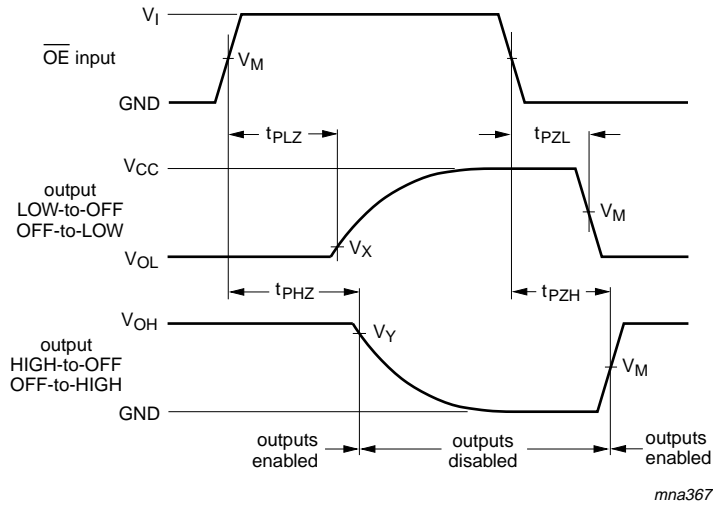
11. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 5. Propagation delay input (An, Bn) to output (Bn, An)



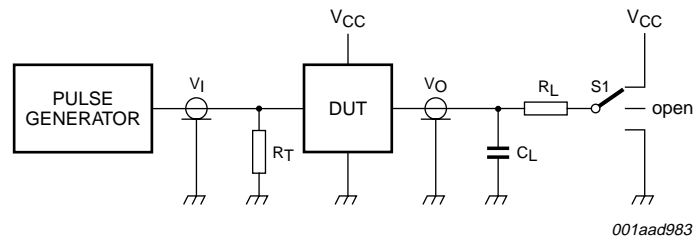
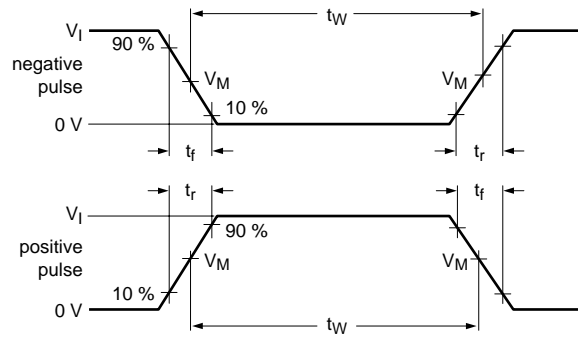
Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. enable and disable times

Table 8: Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74AHC245	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$
74AHCT245	1.5 V	$0.5V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$



001aad983

Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistor

S1 = Test selection switch

Fig 7. Load circuitry for switching times

Table 9: Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC245	V_{CC}	3.0 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74AHCT245	3.0 V	3.0 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

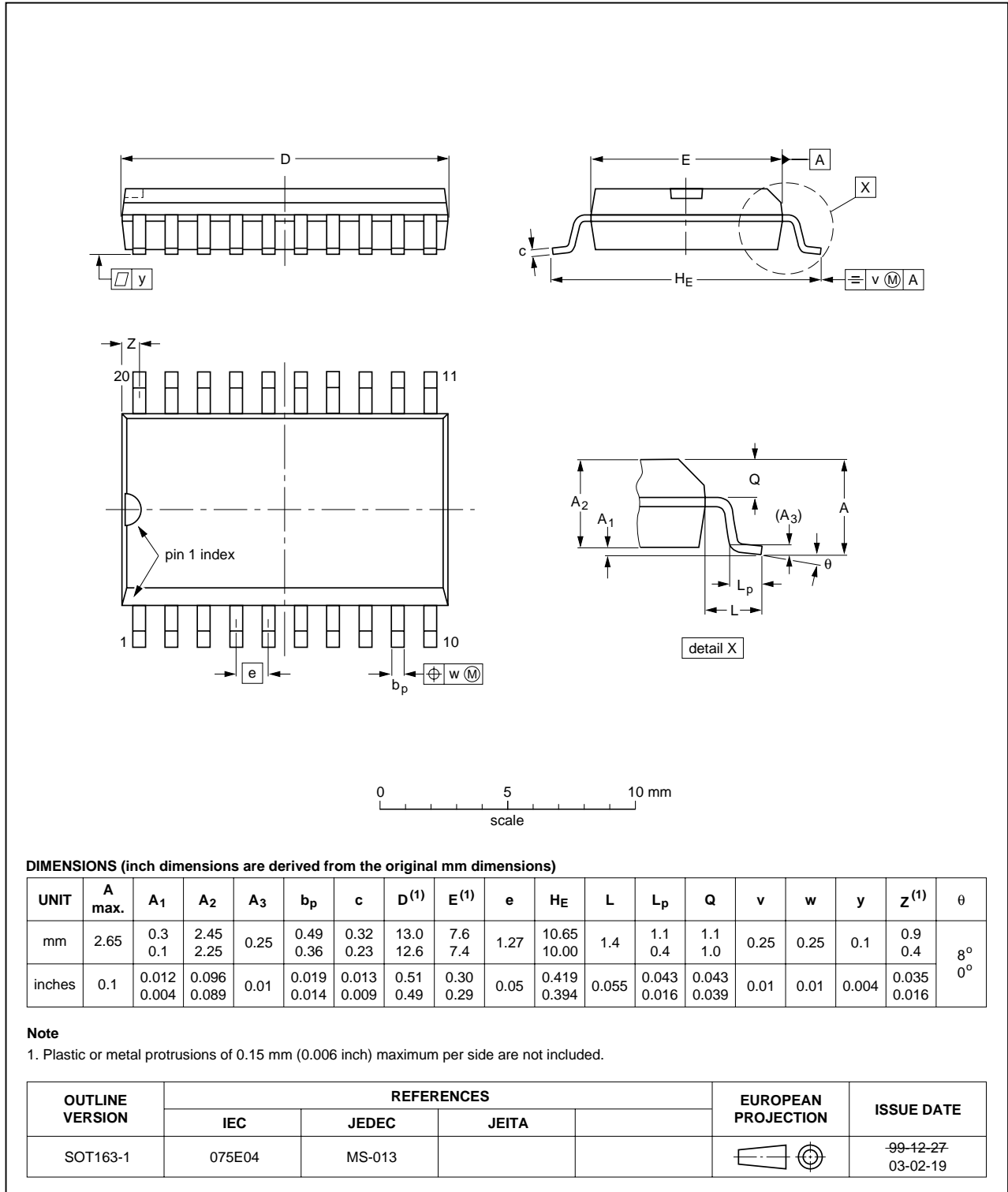


Fig 8. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

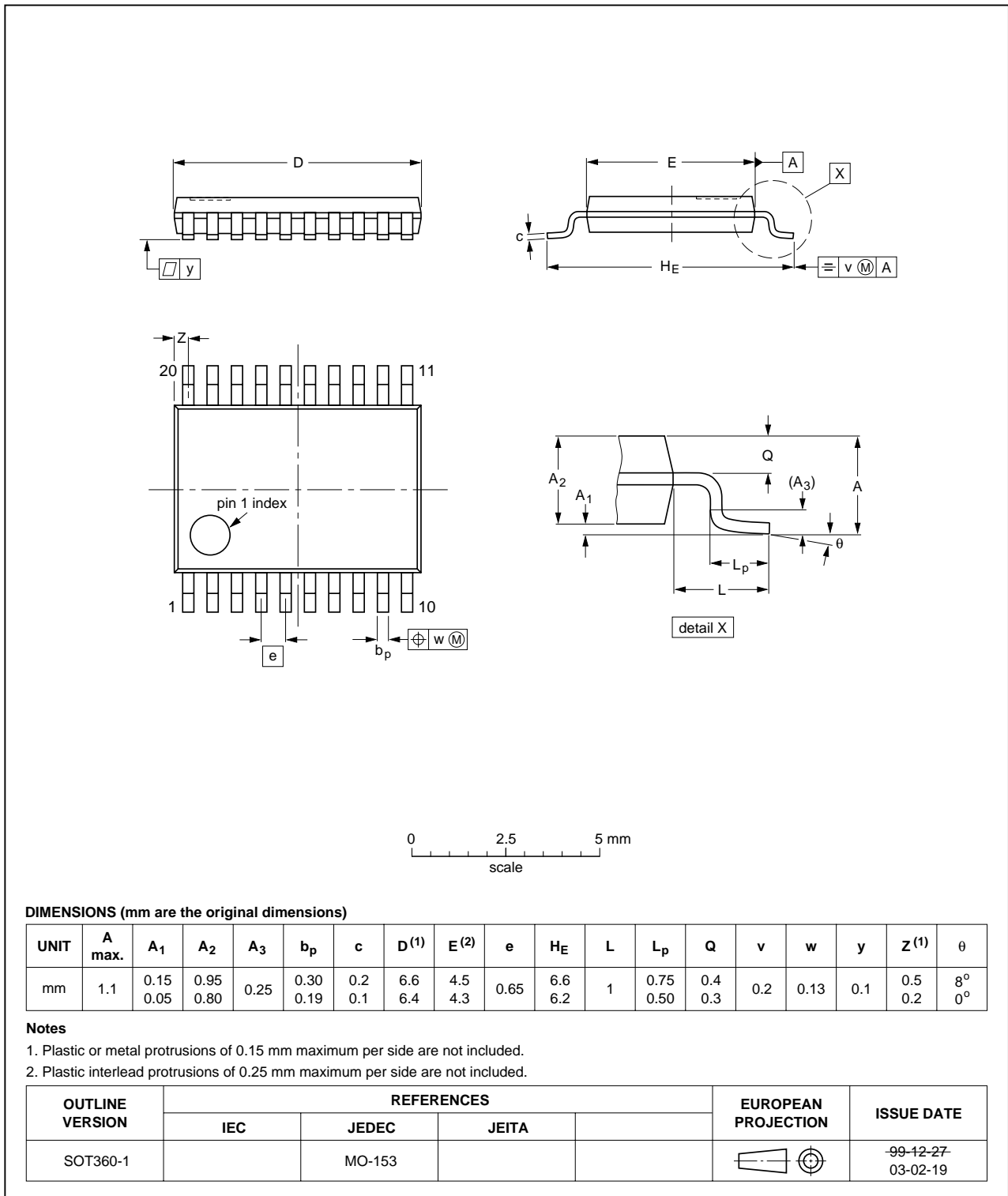


Fig 9. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm

SOT764-1

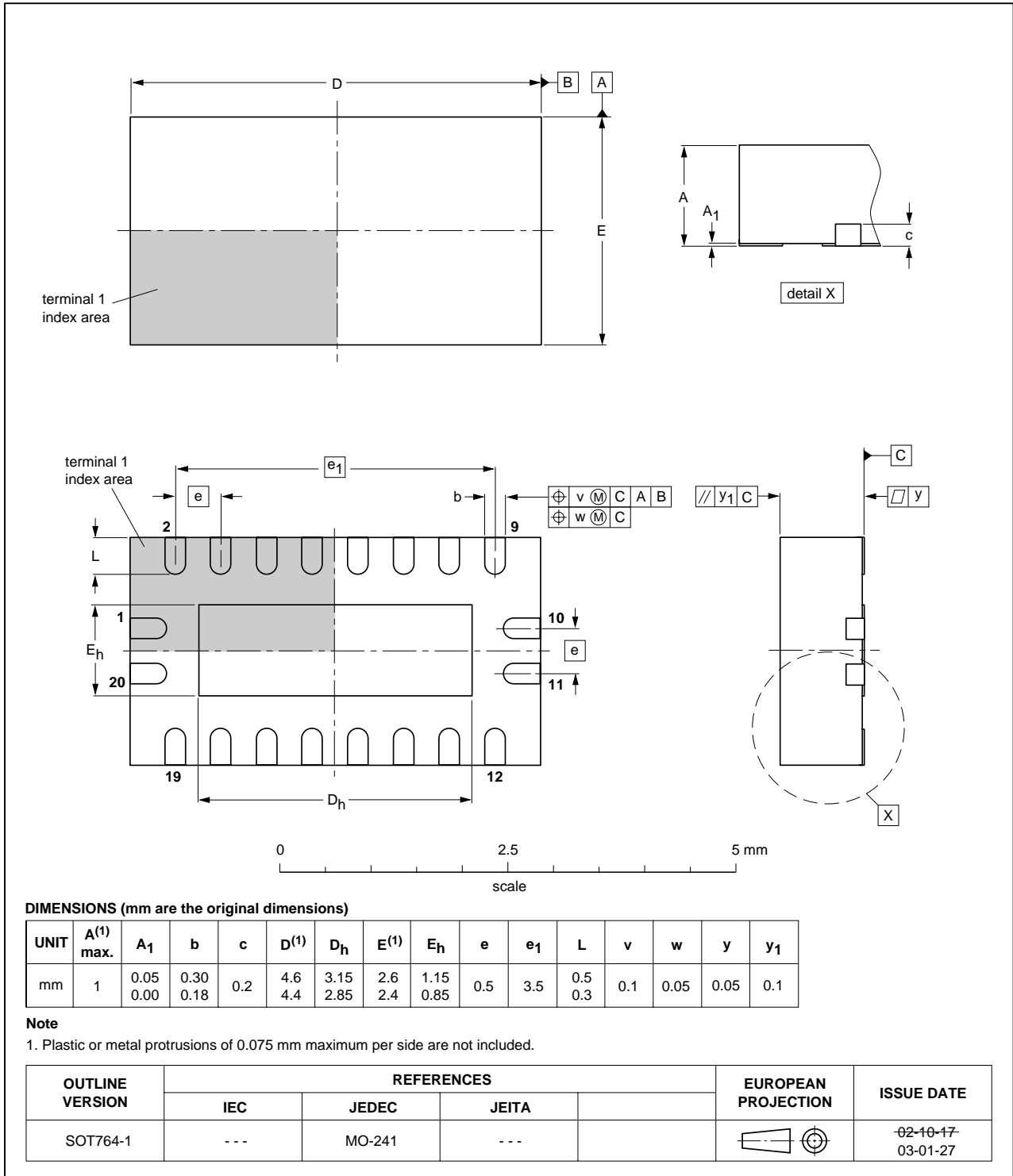


Fig 10. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10: Abbreviations

Acronym	Description
CDM	Charge Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
74AHC_AHCT245_3	20070925	Product data sheet		-	74AHC_AHCT245_2
Modifications:					
					<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name when appropriate. Section 3: DHVQFN20 package added. Section 8: derating values added for DHVQFN20 package. Section 12: outline drawing added for DHVQFN20 package.
74AHC_AHCT245_2	19990928	Product specification	-	939775006297	74AHC_AHCT245_1
74AHC_AHCT245_1	19980921	Product specification	-	939775004255	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 25 September 2007
 Document identifier: 74AHC_AHCT245_3